

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of manufacturing a semiconductor device, said method comprising the steps of:

forming a silicon oxide film on a first single crystal silicon substrate;

~~forming a hydrogen added layer by adding hydrogen to [[a]] the first single crystal silicon substrate through the silicon oxide film to form a hydrogen added layer in the first single crystal silicon substrate from a major surface side thereof, said first single crystal substrate having a silicon oxide film on the major surface;~~

bonding the first single crystal silicon substrate to a second substrate through the silicon oxide film with a bonded interface therebetween, said second substrate being as a support;

separating the first single crystal silicon substrate by a first heat treatment;

carrying out a second heat treatment to a single crystal silicon film which remains on the second substrate in the separating step so that the bonded interface becomes stable wherein trap levels and defects are generated due to the second heat treatment;

flattening a [[major]] surface of the single crystal silicon film;

forming a silicon island by patterning the single crystal silicon film after carrying out the second heat treatment; and

thermally oxidizing the silicon island ~~in order to eliminate~~ reduce the trap levels and defects from the silicon island.

2. (Canceled)

3. (Original) A method according to claim 1, wherein the thermally oxidizing step is carried out at a temperature in a range of from 1050 to 1150° C.

4. (Original) A method according to claim 1, wherein the thermally oxidizing step is carried out in an oxidizing atmosphere comprising a halogen element.

5.-6. (Canceled)

7. (Original) A method according to claim 1, wherein said semiconductor device is one selected from the group consisting of a D/A converter, a γ correction circuit, and a signal dividing circuit.

8. (Original) A method according to claim 1, wherein said semiconductor device is one selected from the group consisting of a liquid crystal display device, an EL (electroluminescence) display device and an EC (electrochromic) display device.

9. (Original) A method according to claim 1, wherein said semiconductor device is a microprocessor.

10. (Previously Presented) A method according to claim 1, wherein said semiconductor device is a computer for controlling a vehicle such as a car or an electric train.

11. (Original) A method according to claim 1, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector (rear type or front type), a head mount display (a goggle type display), a car navigation system, a personal computer, a portable information terminal such as a mobile computer, a portable telephone, or an electric book.

12.-16. (Canceled)

17. (New) A method of manufacturing a semiconductor device, said method comprising the steps of:

forming a silicon oxide film on a first single crystal silicon substrate;

adding hydrogen to the first single crystal silicon substrate through the silicon oxide film to form a hydrogen added layer in the first single crystal silicon substrate;

bonding the first single crystal silicon substrate to a second substrate through the silicon oxide film with a bonded interface therebetween, said second substrate being as a support wherein said second substrate is a quartz substrate;

separating the first single crystal silicon substrate by a first heat treatment;

carrying out a second heat treatment to a single crystal silicon film which remains on the second substrate in the separating step so that the bonded interface becomes stable wherein trap levels and defects are generated due to the second heat treatment;

forming a silicon island by patterning the single crystal silicon film after carrying out the second heat treatment; and

thermally oxidizing the silicon island to reduce the trap levels and the defects from the silicon island.

18. (New) A method according to claim 17, wherein the thermally oxidizing step is carried out at a temperature in a range of from 1050 to 1150° C.

19. (New) A method according to claim 17, wherein the thermally oxidizing step is carried out in an oxidizing atmosphere comprising a halogen element.

20. (New) A method according to claim 17, wherein said semiconductor device is one selected from the group consisting of a D/A converter, a γ correction circuit, and a signal dividing circuit.

21. (New) A method according to claim 17, wherein said semiconductor device is one selected from the group consisting of a liquid crystal display device, an EL (electroluminescence) display device and an EC (electrochromic) display device.

22. (New) A method according to claim 17, wherein said semiconductor device is a microprocessor.

23. (New) A method according to claim 17, wherein said semiconductor device is a computer for controlling a vehicle such as a car or an electric train.

24. (New) A method according to claim 17, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector (rear type or front type), a head mount display (a goggle type display), a car navigation system, a personal computer, a portable information terminal such as a mobile computer, a portable telephone, or an electric book.

25. (New) A method of manufacturing a semiconductor device, said method comprising the steps of:

forming a silicon oxide film on a first single crystal silicon substrate;

adding hydrogen to the first single crystal silicon substrate through the silicon oxide film to form a hydrogen added layer in the first single crystal silicon substrate;

bonding the first single crystal silicon substrate to a second substrate through the silicon oxide film with a bonded interface therebetween, said second substrate being as a support wherein said second substrate is a silicon substrate;

separating the first single crystal silicon substrate by a first heat treatment;

carrying out a second heat treatment to a single crystal silicon film which remains on the second substrate in the separating step so that the bonded interface becomes stable wherein trap levels and defects are generated due to the second heat treatment;

forming a silicon island by patterning the single crystal silicon film after carrying out the second heat treatment; and

thermally oxidizing the silicon island to reduce the trap levels and the defects from the silicon island.

26. (New) A method according to claim 25, wherein the thermally oxidizing step is carried out at a temperature in a range of from 1050 to 1150° C.

27 (New) A method according to claim 25, wherein the thermally oxidizing step is carried out in an oxidizing atmosphere comprising a halogen element.

28. (New) A method according to claim 25, wherein said semiconductor device is one selected from the group consisting of a D/A converter, a γ correction circuit, and a signal dividing circuit.

29. (New) A method according to claim 25, wherein said semiconductor device is one selected from the group consisting of a liquid crystal display device, an EL (electroluminescence) display device and an EC (electrochromic) display device.

30. (New) A method according to claim 25, wherein said semiconductor device is a microprocessor.

31. (New) A method according to claim 25, wherein said semiconductor device is a computer for controlling a vehicle such as a car or an electric train.

32. (New) A method according to claim 25, wherein said semiconductor device is one selected from the group consisting of a video camera, a digital camera, a projector (rear type or front type), a head mount display (a goggle type display), a car navigation system, a personal computer, a portable information terminal such as a mobile computer, a portable telephone, or an electric book.